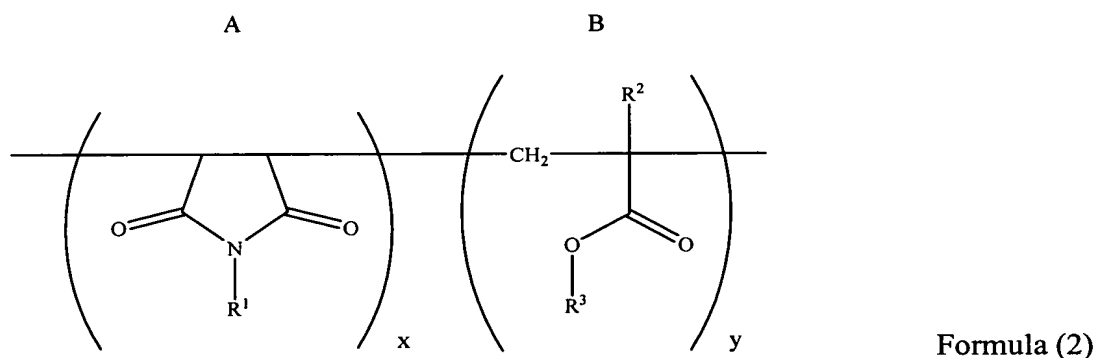


Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-3. (Canceled)

4. (Currently Amended) A bottom anti-reflective coat forming composition for lithography processes in semiconductor device preparation, wherein the bottom anti-reflective coat forming composition comprises resin containing a structural unit comprising maleimide or a derivative thereof~~The bottom anti-reflective coat forming composition according to claim 1,~~ wherein the resin comprises the structural unit shown in Formula (2)



wherein each R^1 , R^2 and R^3 is independent of one another; R^1 is hydrogen, halogen, or substituted or unsubstituted C_1 - C_{10} alkyl group ~~or benzene derivatives~~; R^2 is hydrogen, halogen or methyl group; R^3 is hydrogen or substituted or unsubstituted C_1 - C_{10} alkyl group; x is number 1-10300; and y is number 0-12100, and is the polymer comprising 10-100 mol% of the maleimide structural unit (A) and 90-0 mol% of the (meth)acrylate structural unit (B), based on the sum of the maleimide structural unit (A) and the (meth)acrylate structural unit (B) in the ~~polymer~~ polymer, and

wherein said composition further comprises crosslinking agent having at least two crosslinking forming functional groups.

5. (Original) The bottom anti-reflective coat forming composition according to claim 4, wherein the maleimide structural unit (A) is 51-95 mol% and the (meth)acrylate structural unit (B) is 49-5 mol% in the structural unit shown in the Formula (2).

6. (Currently Amended) The bottom anti-reflective coat forming composition according ~~claim 3, wherein~~ claim 4, wherein R¹ is hydrogen, halogen or substituted or unsubstituted C₁-C₁₀ alkyl group in the structural unit shown in the Formula (1) or the Formula (2).

7. (Canceled)

8. (Currently Amended) ~~The A method of forming the a bottom anti-reflective coating for the lithography process-processes in the semiconductor device preparation of semiconductor device, comprising applying the bottom anti-reflective coat forming composition according to claim 1~~ claim 4 over the a substrate, and then baking.

9. (Currently Amended) ~~The A method of the semiconductor device preparation for semiconductor device, comprising:~~

_____ applying the bottom anti-reflective coat forming composition according to claim 1 claim 4 over the a substrate,

_____ baking the coated substrate to form a ~~forming the~~ bottom anti-reflective coating upon baking,

_____ coating photoresist over said bottom anti-reflective coating,

_____ exposing said substrate to form an image,

_____ transferring the image over the substrate by etching, and

_____ developing and forming integrated circuit elements ~~after transferring the image over the substrate by etching.~~

10. (Currently Amended) The method of ~~the~~ semiconductor device preparation for ~~semiconductor device~~ according to claim 9, wherein exposure is conducted with ~~the~~ light at 193 nm wave-length.